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ev. 04/03

Docket No. ELM-1 Cont. 10

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Glenn J. Leedy

Application No.: 10/700,429 Confirmation No.: 5639

Filed : November 3, 2003

For : MEMBRANE IC FABRICATION (AS AMENDED)

Group Art Unit: 3729

Examiner : Not yet assigned

New York, New York

July 8, 2004

Hon. Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450

TRANSMITTAL LETTER FOR INFORMATION DISCLOSURE STATEMENT

Sir:

Transmitted herewith is an Information Disclosure
Statement in the above-identified application. This
Statement is submitted:

- [] within three months of the application filing date;
- [X] more than three months from the application filing date but before the mailing date of the first Office Action on the merits.

In accordance with 37 C.F.R. § 1.97, submission of this Statement requires no fee. However, if for any reason a fee is due, the Director is hereby authorized to charge payment of any fees required in connection with this

Information Disclosure Statement to Deposit Account No. 06-1075. A duplicate copy of this letter is transmitted herewith.

Respectfully submitted,

Philip R. Poh

Registration No. 51,176

Agent for Applicants

FISH & NEAVE

Customer No. 1473

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New York, New York 10020-1105

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I hereby certify that this Correspondence is being deposited with the U.S. Postal Service as First Class Mail in an envelope

Addressed to: Commissioner for Patents

P.O. Box 1450

Claire J

Alexandria, VA 22313-1450 on

Signature of Person Signing

ELM-1 Cont.10

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Glenn J. Leedy

Application No.: 10/700,429 Confirmation No.: 5639

: November 3, 2003 Filed

: MEMBRANE IC FABRICATION (AS AMENDED) For

Group Art Unit : 3729

Examiner : Not yet assigned

Hon. Commissioner for Patents

P.O. Box 1450

Alexandrian, Virginia 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

In accordance with 37 C.F.R. §§ 1.56 and 1.97, applicant wishes to call the attention of the Examiner to the following documents:

U.S. Patents

Re. 34,893	04/04/95
2,915,722	12/01/59
3,202,948	08/24/65
3,559,282	02/02/71
3,560,364	02/02/71
3,602,982	09/07/71
3,615,901	10/26/71
3,716,429	02/13/73
3,777,227	12/14/73
3,868,565	02/25/75
3,922,705	11/25/75
3,997,381	12/14/76
4,070,230	01/24/78
	2,915,722 3,202,948 3,559,282 3,560,364 3,602,982 3,615,901 3,716,429 3,777,227 3,868,565 3,922,705 3,997,381

		/ /
Greenwood et al.	4,131,985	01/02/79
Hauser, Jr., et al.	4,142,004	02/27/79
Hoeberechts	4,251,909	02/24/81
	•	•
Kubacki	4,262,631	04/21/81
Shioya et al.	4,394,401	07/19/83
Trenkler et al.	4,401,986	08/30/83
Thomas et al.	4,416,054	11/22/83
Takagi et al.	4,539,068	09/03/85
Reid et al.	4,585,991	04/29/86
Yasumoto et al.	4,612,083	09/16/86
Belanger et al.	4,617,160	10/14/86
Shimizu et al.	4,618,397	10/21/86
Schmitz	4,618,763	10/21/86
Christensen	4,663,559	05/05/87
Burns et al.	4,684,436	08/04/87
Hatada	4,693,770	09/15/87
Maeda et al.	4,702,336	10/27/87
Seibert et al.	4,702,936	10/27/87
Go	4,706,166	11/10/87
Stevenson	4,721,938	01/26/88
Reid	4,761,681	08/02/88
		• •
Holmen et al.	4,784,721	11/15/88
Freeman	4,810,673	03/07/89
Mattox et al.	4,825,277	04/25/89
Tam et al.	4,857,481	08/15/89
Leedy	4,924,589	05/15/90
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Borel et al.	4,940,916	07/10/90
Borel et al.	ReB14,940916	11/26/96
Vranish et al.	4,950,987	08/21/90
Lee et al.	4,952,446	08/18/90
Rokos	4,954,865	09/04/90
Shinomiya	4,957,882	09/18/90
Young et al.	4,965,415	10/23/90
Mauger	4,966,663	10/30/90
Leedy	4,994,735	02/19/91
Keogh et al.	5,008,619	04/16/91
_		
Allen et al.	5,010,024	04/23/91
Leedy	5,020,219	06/04/91
Leedy	5,034,685	07/23/91
Greenwald et al.	5,070,026	12/03/91
Findler et al.		12/10/91
	5,071,510	•
Machado et al.	5,098,865	03/24/92
Leedy	5,103,557	04/14/92
Mauger	5,110,373	05/05/92
Eichelberger	5,111,278	05/05/92
Chan et al.	5,116,777	05/26/92
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JAPAN	JP 04-083371	03/1992
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"IC Tower Patent: Simple Technology Receives Patent on the IC Tower, a Stacked Memory Technology," http://www.simpletech.com/whatsnew/memory/@60824.htm (1998).

Alloert, K., et al., "A Comparison Between Silicon Nitride Films Made by PCVD of N_2 -SiH $_4$ / A_r and N_2 -SiH $_4$ /He," Journal of the Electrochemical Society, Vol. 132, No. 7, pp. 1763-1766, (July 1985).

Hendricks, et al., "Polyquinoline Coatings and Films: Improved Organic Dielectrics for IC's and MCM's," Eleventh IEEE/CHMT International Electronics Manufacturing Technology Symposium," pp. 361-265 (1991).

Knolle, W.R., et al., "Characterization of Oxygen-Doped, Plasma-Deposited Silicon Nitride," Journal of the Electrochemical Society, Vol. 135, No. 5, pp. 1211-1217, (May 1988).

Nguyen, S.V., "Plasma Assisted Chemical Vapor Deposited Thin Films for Microelectronic Applications, J. Vac. Sci. Technol. Vol. B4, No. 5, pp.1159-1167, (Sep/Oct. 1986).

Olmer, et al., "Intermetal Dielectric Deposition by Plasma Enhanced Chemical Vapor Deposition," Fifth IEEE/CHMT International Electronic Manufacturing Technology Symposium - Design-to-Manufacturing Transfer Cycle," pp. 98-99 (1988).

Runyan, W.R., "Deposition of Inorganic Thin Films," Semiconductor Integrated Circuit Processing Technology, p. 142 (1990).

Sze, S.M., "Surface Micromachining," Semiconductor Sensors, pp. 58-63 (1994).

Vossen, John L., "Plasma-Enhanced Chemical Vapor Deposition," Thin Film Processes II, pp. 536-541 (1991).

Wolf, Stanley, "Basic of Thin Films," Silicon Processing for the VLSI Era, pp. 115, 192-193 and 199 (1986).

Copies of the aforementioned documents are listed on the accompanying Form PTO-1449 (submitted in duplicate).

It is respectfully requested that these documents be:

(1) fully considered by the Patent and Trademark Office
during the examination of this application; and (2) printed
on any patent which may issue on this application.

Applicant requests that a copy of Form PTO-1449, as
considered and initialized by the Examiner, be returned with
the next communication.

Consideration of the foregoing in relation to this patent application is respectfully requested.

Respectfully submitted,

Registration No. 51,176

1251 Avenue of the Americas

New York, New York 10020-1104

Agent for Applicant

Tel.: (212) 596-9000

Customer No. 1473

Philip R. Poh

FISH & NEAVE

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Addressed to:

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450 on

Claire J Salmil-Van Googygan

Signature of Person Signing

6



U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

ATTY. DOC ELM-1 Cont		APPLICATION NO. 10/700,429
APPLICANT Glenn J. Le		CONFIRMATION NO. 5639
FILING DAT November 3	_	GROUP 3729
1		

U.S. PATENT DOCUMENTS

EXAMINE R INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	Re. 34,893	04/04/95	Fujii et al.	257	419	
	2,915,722	12/01/59	Foster	336	115	
	3,202,948	08/24/65	Farrand	336	115	
	3,559,282	02/02/71	Lesk	438	113	
	3,560,364	02/02/71	Burkhardt	324	207.12	
	3,602,982	09/07/71	Emmasingel	29	577	
	3,615,901	10/26/71	Medicus	148	11.5 R	
	3,716,429	02/13/73	Napoli et al.	156	17	
	3,777,227	12/14/73	Krishna et al.	257	578	
	3,868,565	02/25/75	Kuipers	324	207.26	
	3,922,705	11/25/75	Yerman	357	26	
	3,997,381	12/14/76	Wanlass	156	3	
	4,070,230	01/24/78	Stein	156	657	
	4,131,985	01/02/79	Greenwood et al.	29	580	
	4,142,004	02/27/79	Hauser, Jr. et al.	438	792	
	4,251,909	02/24/81	Hoeberechts	29	580	
	4,262,631	04/21/81	Kubacki	118	723MP	
	4,394,401	07/19/83	Shioya et al.	427	574	
	4,401,986	08/30/83	Trenkler et al.	340	870.32	
	4,416,054	11/22/83	Thomas et al.	29	572	
	4,539,068	09/03/85	Takagi et al.	156	614	
	4,585,991	04/29/86	Reid et al.	324	158 P	
	4,612,083	09/16/86	Yasumoto et al.	156	633	
	4,617,160	10/14/86	Belanger et al.	264	40.1	
	4,618,397	10/21/86	Shimizu et al.	156	628	
	4,618,763	10/21/86	Schmitz	250	211R	
	4,663,559	05/05/87	Christensen	313	336	
	4,684,436	08/04/87	Burns et al.	216	65	
	4,693,770	09/15/87	Hatada	156	151	

EXAMINER

		FOF COMMERCE DEMARK OFFICE	ATTY. DOC ELM-1 Con		APPLICATION NO. 10/700,429
	ION DISCLOS		APPLICANT Glenn J. Leedy		CONFIRMATION NO. 5639
STATEMEN		ZAIVI	FILING DAT November 3		GROUP 3729
· · · · · · · · · · · · · · · · · · ·					
4,702,336	10/27/87	Maeda et al.	180	197	
4,702,936	10/27/87	Seibert et al.	427	583	
4,706,166	11/10/87	Go	361	403	
4,721,938	01/26/88	Stevenson	338	4	
4,761,681	08/02/88	Reid	357	68	
4,784,721	11/15/88	Holmen et al.	156	647	
4,810,673	03/07/89	Freeman	438	386	
4,825,277	04/25/89	Mattox et al.	257	639	
4,857,481	08/15/89	Tam et al.	438	619	
4,924,589	05/15/90	Leedy	438	6	
4,940,916	07/10/90	Borel et al.	313	306	
Re B14,940,916	11/26/96	Borel et al.	315	306	
4,950,987	08/21/90	Vranish et al.	324	207.23	
4,952,446	08/18/90	Lee et al.	428	220	
. 4,954,865	09/04/90	Rokos	257	378	
4,957,882	09/18/90	Shinomiya	438	65	
4,965,415	10/23/90	Young et al.	200	83 N	
4,966,663	10/30/90	Mauger	205	656	
4,994,735	02/19/91	Leedy	324	158	
5,008,619	04/16/91	Keogh et al.	324	207.17	
5,010,024	04/23/91	Allen et al.	438	659	
5,020,219	06/04/91	Leedy	29	846	
5,034,685	07/23/91	Leedy	324	158 F	
5,070,026	12/03/91	Greenwald et al.	437	3	
5,071,510	12/10/91	Findler et al.	156	647	
5,098,865	03/24/92	Machado et al.	438	788	
5,103,557	04/14/92	Leedy	29	832	
5,110,373	05/05/92	Mauger	148	33.2	
5,111,278	05/05/92	Eichelberger	357	75	
5,116,777	05/26/92	Chan et al.	438	234	
5,130,894	07/14/92	Miller	361	393	
5,132,244	07/21/92	Roy	438	477	

FORM PTO-1449		ENT OF COMMERCI RADEMARK OFFICE		DOCKET NO. Cont. 10	APPLICATION NO. 10/700,429	
	FORMATION DISC			APPLICANT CONFIRM 5639		
3	TATEMENT BY AFT	LICANT		DATE nber 3, 2003	GROUP 3729	
•						
5,151,	775 09/29/9	2 Hadwin	357	80		
. 5,156,						
5,203,			445	5 24		
5,225,		<u> </u>	324	158		
5,236,			228			
5,262,	- 171		437			
5,270,			437			
5,273,			437			
5,274,		1	257	758		
5,279,			427			
5,284,			437	183		
5,323,			257	48		
5,324,			437	225		
5,354,			438	3 411		
5,363,			315	366		
5,385,			156			
5,385,		Nelson et al.	514	291		
5,420,		95 Shimoji	257	622		
5,424,			36	735		
5,426,		95 Finnila	437	208		
5,426,		Akagi et al.	324	239		
5,432,	444 07/11/	95 Yasohama et al	. 324	240		
5,432,			365	63		
5,434,		T	324	67		
5,451,			430	i i		
5,453,			437	203		
5,457,			29	895		
5,476,			437	132		
5,489,			437	208		
5,502,	667 03/26/		365	5 51		
5,512,			430	30		
5,527,		Pati et al.	430) 5		

FORM PTO-1449	U.S. DEPARTMEN PATENT AND TRA	T OF COMMERCE	ATTY. DOC ELM-1 Cont		APPLICATION NO. 10/700,429		
	FORMATION DISCLO		APPLICANT Glenn J. Le		CONFIRMATION NO. 5639		
5	TATEMENT OF APPLI	CANT	FILING DAT November 3		GROUP 3729		
5,529,	829 06/25/96	Koskenmaki et al.	428	167			
. 5,534,		Frye et al.	437	209			
5,555,		Toshiaki et al.	365	200			
5,563,		Ramm et al.	437	51			
5,571,		Leedy	437	51			
5,580,		Leedy	430	5			
5,581,		Ludwig et al.	365	63			
5,582,		Pierrat	430	5			
5,583,	688 12/10/96	Hornbeck	359	291			
5,592,	007 01/07/97	Leedy	257	347			
5,592,		Leedy	257	619			
5,595,		Heijboer	439	20			
5,606,	186 02/25/97	Noda	257	226			
5,627,	112 05/06/97	Tennant et al.	438	113			
5,629,	137 05/13/97	Leedy	430	313			
5,633,	209 05/27/97	Leedy	435	228			
. 5,637,	536 06/10/97	Val	438	686			
5,654,	127 08/05/97	Leedy	430	315			
5,654,	220 08/05/97	Leedy	438	25			
5,656,	552 08/12/97	Hudak et al.	438	15			
5,675,	185 10/07/97	Chen et al.	257	774			
5,694,	588 12/02/97	Ohara et al.	395	566			
5,725,	995 03/10/98	Leedy	430	315			
5,750,	211 05/12/98	Weise et al.	427	579			
5,760,	478 06/02/98	Bozso et al.	257	777			
5,773,	152 06/30/98	Okonogi	428	446			
5,786,		Rolfson	430	5			
5,793,	115 08/11/98	Zavracky et al.	257	777			
5,831,	280 11/03/98	Ray	257	48			
5,834,	334 11/10/98	Leedy	438	107			
5,840,	593 11/24/98	Leedy	438	6			
5,856,	695 01/05/99	Ito et al.	257	370			

FORM PTO-				OF COM			ATTY. DOCKET NO. APPLICATION 10/700,429			N NO.	
	INFORMATIO	ON DISC	LOS	URE						CONFIRMATION NO. 5639	
	STATEMENT	FBY AP	PLIC	ANT		FILING DATE November 3, 2003				GROUP	
			-								
	5,868,949	02/09/	99	Sotokaw	a et al.		216	18			-,,-,-
	5,869,354	02/09/	99	Leedy			438	110			
	5,870,176	02/09/		Sweatt e	t al.	T	355	53			
	5,880,010	03/09/		Davidsor			438	455			
	5,882,532	03/16/	99	Field et a	 al.	\Box	216	2		•	
	5,902,118	05/11/		Hübner	· ··· ·		438	106			
	5,915,167	06/22/		Leedy			438	108			
	5,946,559	08/31/	o	Leedy			438	157			
	5,985,693 11/16						438	107			
	5,998,069	12/07/	99	al.		430	5				
	6,008,126	12/28/	99				438	667			
	6,020,257	02/01/	00				438	626			
	6,045,625	04/04/	04/04/00 Houston 07/04/00 Adamic, Jr.			148 33.3 257 506 257 777					
	6,084,284	07/04/			Jr.				·		
_	6,097,096	08/01/									
-	6,133,640	10/17/	00	Leedy			257	778			
	6,194,245 B1	02/27/	01	01 Tayanaka			438	57			
·	6,197,456 B1	03/06/	01				430	5			
	6,208,545 B1	03/27/	01				365	51			
	6,236,602 B1	05/22/	01	Patti			365	201			
	6,261,728 B1	07/17/	01				430	30			
	6,288,561 B1	09/11/	01	Leedy			324 760				
	6,294,909 B1	09/25/	01	Leedy			324	207.17			
		· ·	FO	REIGN P	ATENT DOCU	MEN	NTS				
EXAMINER INITIAL	DOCUMENT NU	IMBER	ַ	DATE	COUNTRY		CLASS	SUBCLA	ss -	TRANSI YES	ATION NO
	WO 98/19337		05/	1998	PCT	Н	01L	21/44			
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